

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7041	(word near5 line).clm.	US-PGPU B	OR	ON	2007/09/13 22:34
L2	193897	(substrate wafer).clm.	US-PGPU B	OR	ON	2007/09/13 22:34
L3	97293	(nitride oxide).clm.	US-PGPU B	OR	ON	2007/09/13 22:35
L4	43133	(etch\$3).clm.	US-PGPU B	OR	ON	2007/09/13 22:35
L5	3781	(active near3 area).clm.	US-PGPU B	OR	ON	2007/09/13 22:36
L6	22284	(dopant impurity).clm.	US-PGPU B	OR	ON	2007/09/13 22:36
L7	69382	(isolat\$3).clm.	US-PGPU B	OR	ON	2007/09/13 22:36
L8	23	1 and 2 and 3 and 4 and 5 and 6 and 7	US-PGPU B	OR	ON	2007/09/13 22:37

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L1	26944	gate near10 (oxide and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))))	US-PGPU B; USPAT; USOCR	OR	ON	2007/09/13 16:53
L2	56	L1 and (common near5 mask\$3 near5 step)	US-PGPU B; USPAT; USOCR	OR	ON	2007/09/13 16:53
L3	92	(((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3")))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS) and PMOS) and ((etch\$3 pattern\$3) with oxide with nitride with rate)	US-PGPU B; USPAT	OR	ON	2007/09/13 16:54
L4	11521	gate and (oxide and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4"))))	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/09/13 16:53
L5	26	L4 and (common and mask\$3 and step)	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/09/13 16:53
L6	2	(((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3")))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS) and PMOS) and ((etch\$3 pattern\$3) and oxide with nitride and rate)	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/09/13 16:55

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L7	2	(((((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")))) and (oxide (silicon and oxide) SiO2 ("Si" adj3 "O.sub.2")))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS) and PMOS) and ((etch\$3 pattern\$3) and oxide with nitride and rate)	FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2007/09/13 16:56
L8	2511	(((((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")))) and (oxide (silicon and oxide) SiO2 ("Si" adj3 "O.sub.2")))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS) and PMOS) and ((etch\$3 pattern\$3) and oxide with nitride and rate)	US-PGPU B; USPAT; USOCR	OR	ON	2007/09/13 16:56
L9	879	8 and ((contact open\$3 via hole) near20 (nitride oxide) near20 (gate source drain))	US-PGPU B; USPAT; USOCR	OR	ON	2007/09/13 16:58
L10	807	9 and (mask resist photoreist (photo near5 resist) PR)	US-PGPU B; USPAT; USOCR	OR	ON	2007/09/13 16:59
L11	803	10 and etch\$3	US-PGPU B; USPAT; USOCR	OR	ON	2007/09/13 16:59